

What is claimed is:

1. A wiring structure of a semiconductor device, comprising:
 - a body formed of a first conductive material in a first insulating film on a semiconductor substrate; and
 - a protrusion formed of a second conductive material in a second insulating film formed on the first insulating film, the protrusion being connected to an upper surface of the body and formed to have a width less than a width of the body, and including a planarized upper surface.
2. The wiring structure of claim 1, wherein the body has a shape of a polygonal column.
3. The wiring structure of claim 1, wherein the body has a shape of a hemispherical column.
4. The wiring structure of claim 1, wherein the first conductive material is one selected from a group consisting of tungsten, aluminum, tungsten alloy, and aluminum alloy.
5. The wiring structure of claim 1, wherein the second conductive material is one selected from a group consisting of tungsten, aluminum, tungsten alloy, and aluminum alloy.
6. The wiring structure of claim 1, wherein the semiconductor device is an SRAM device and the wiring is a v_{ss} line or a word line.
7. The wiring structure of claim 1, wherein the first insulating film is formed of a material having an etching rate greater than that of the second insulating film.
8. The wiring structure of claim 1, further comprising a conductive stud insulated from the wiring by the first insulating film and the second insulating film, connected to the semiconductor substrate, and having a planarized surface having the same height as the planarized surface of the wiring.